

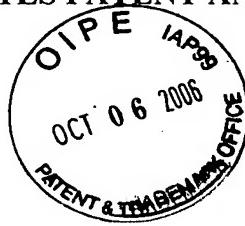
Tfw/2811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Masanobu ANDO, et al.

Serial No.: 10/564,416



Group Art Unit: 2811

Filing Date: January 12, 2006

Examiner: Sara W. Crane

For: LIGHT EMITTING SEMICONDUCTOR DEVICE AND A METHOD OF
MANUFACTURING IT

Honorable Commissioner for Patents
Alexandria, VA 22313-1450

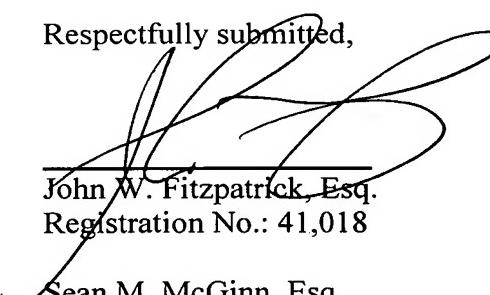
Submission of European Office Action

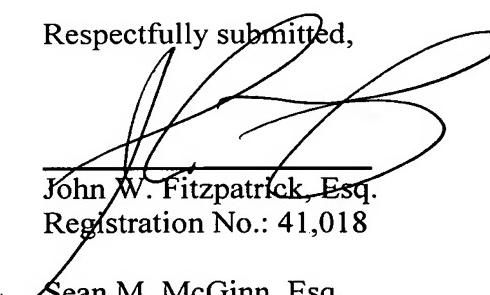
Sir:

Applicants submit the European Search Report dated June 2, 2006, in a counterpart foreign application and listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. The European Office Action refers to references previously made of record in the present case.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,


John W. Fitzpatrick, Esq.
Registration No.: 41,018


Sean M. McGinn, Esq.
Registration No.: 34,386

Date: 10/6/06

McGinn Intellectual Property
Law Group, PLLC
8321 Old Courthouse Road, Suite 200
Vienna, Virginia 22182-3817
(703) 761-4100
Customer No. 21254

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

F05-420-US

Application Number

10/564,416

Applicant(s)

Masanobu ANDO, et al.

Filing Date

January 12, 2006

Group Art Unit

2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	EP-0 662 739	07/12/1995	Europe	Previously submitted	with FDS dated 4/12/06		
	11-026812	01/29/1999	Japan	Previously submitted	with FDS dated 4/12/06		

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

	European Search Report dated June 2, 2006
	Kneissl, Michael, et al., "Continuous-wave ultraviolet InGaN/InAlGaN multiple quantum well laser diodes", Applied Physics Letters, AIP, American Institute of Physics, Melville, NY, US, Vol. 82, No. 15, April 14, 2003, Pages 2386-2388, 012033738 Previously submitted with I DS dated 4/12/06

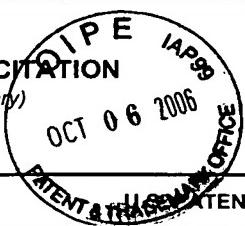
EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



ATTY DOCKET NO.

F05-420-US

APPLICATION NO.

10/564,416

APPLICANT(S)

Masanobu ANDO, et al.

FILING DATE

January 12, 2006

GROUP ART UNIT

2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Nakamura, et al., "InGaN/GaN/AlGaN-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate", Applied Physics Letter, AIP, American Institute of Physics, Melville, NY, US, Vol. 72, No. 2, January 12, 1998 Previously submitted with IBS dated 4/12/06

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.